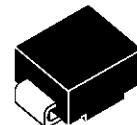


FAST RECOVERY RECTIFIER DIODES

FEATURES

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- SURFACE MOUNT DEVICE



DESCRIPTION

Single high voltage rectifier ranging from 200V to 400 V suited for Switch Mode Power Supplies and other power converters.

SOD6
(Plastic)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$I_{F(RMS)}$	RMS forward current	10	A
$I_{F(AV)}$	Average forward current	1	A
I_{FSM}	Non repetitive surge peak forward current	30	A
T_{stg} T_j	Storage and junction temperature range	- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	SMBYT01-			Unit
		200	300	400	
V_{RRM}	Repetitive peak reverse voltage	200	300	400	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th} (j-l)$	Junction-leads	25	°C/W

SMBYT01

ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V_F *	$T_j = 25^\circ C$	$I_F = 1 A$			1.5	V
	$T_j = 100^\circ C$				1.4	
I_R **	$T_j = 25^\circ C$	$V_R = V_{RRM}$			20	μA
	$T_j = 100^\circ C$				0.5	

Pulse test : * $t_p = 380 \mu s$, duty cycle < 2 %

** $t_p = 5 ms$, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	$T_j = 25^\circ C$	$I_F = 0.5A$	$I_{rr} = 0.25A$		25	ns
		$I_R = 1A$			60	
		$I_F = 1A$	$dI_F/dt = -15A/\mu s$			
		$V_R = 30V$				

TURN-OFF SWITCHING CHARACTERISTICS (Without serie inductance)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
t_{IRM}	$V_{CC} = 200V$	$I_F = 1A$	$L_p \leq 0.05\mu H$		35	50	ns
I_{RM}	$T_j = 100^\circ C$	$dI_F/dt = -50A/\mu s$			1.5	2	A

To evaluate the conduction losses use the following equation :

$$P = 1.1 \times I_{F(AV)} + 0.25 \times I_{F(RMS)}^2$$

Voltage (V)	200	300	400
Marking	B2	B3	B4

Laser marking
Logo indicates cathode

Fig.1 : Low frequency power losses versus average current.

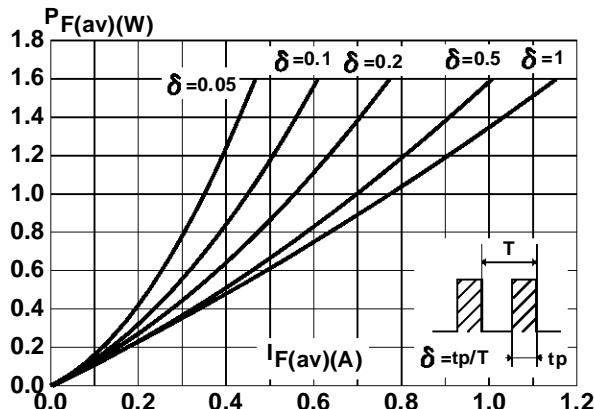


Fig.3 : Non repetitive surge peak forward current versus overload duration.

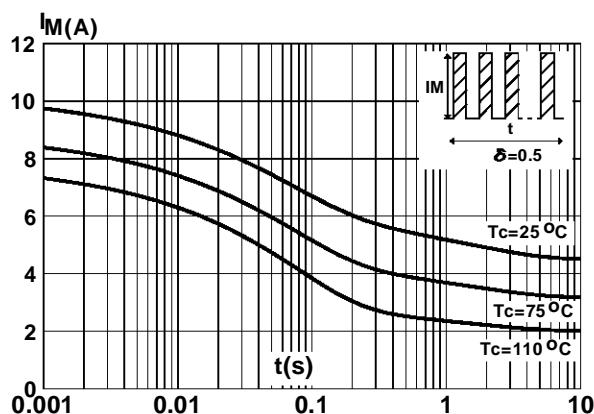


Fig.5 : Voltage drop versus forward current. (Maximum values)

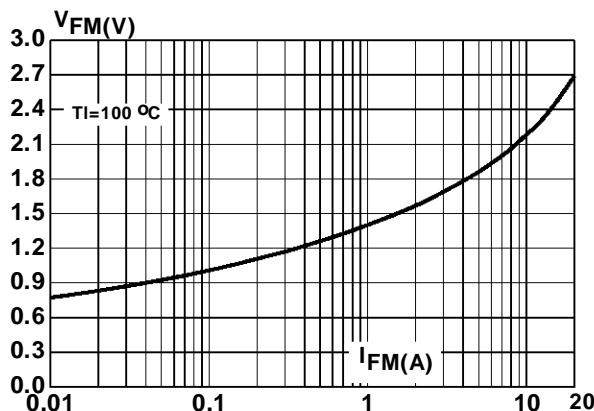


Fig.2 : Peak current versus form factor.

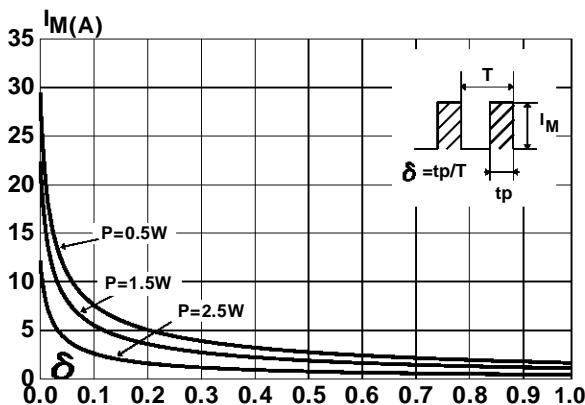


Fig.4 : Relative variation of thermal impedance junction to lead versus pulse duration.

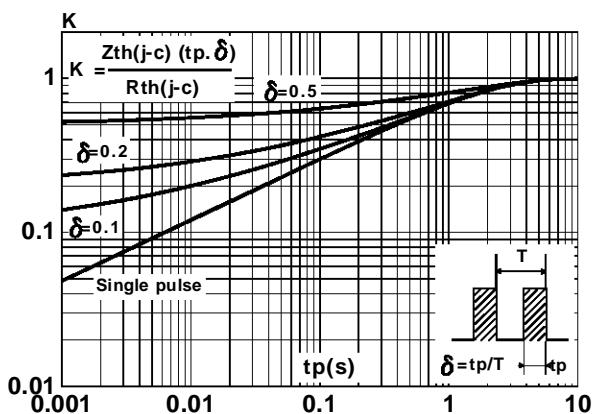
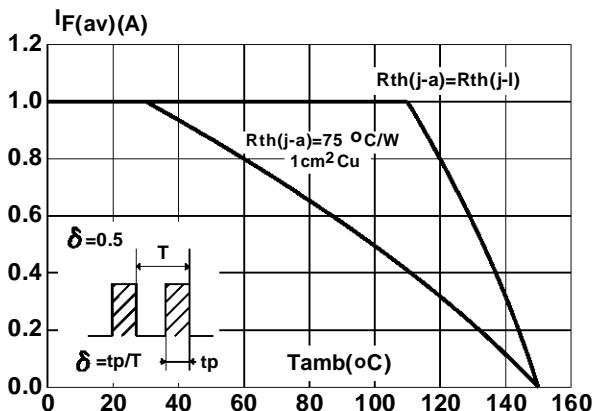


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



SMBYT01

Fig.7 : Recovery time versus dI_F/dt .

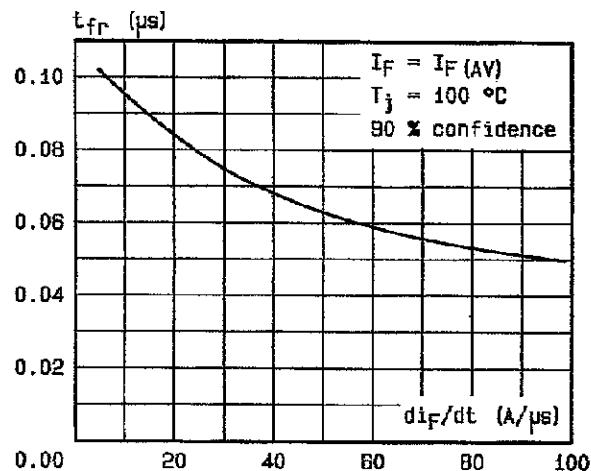


Fig.9 : Peak reverse current versus dI_F/dt .

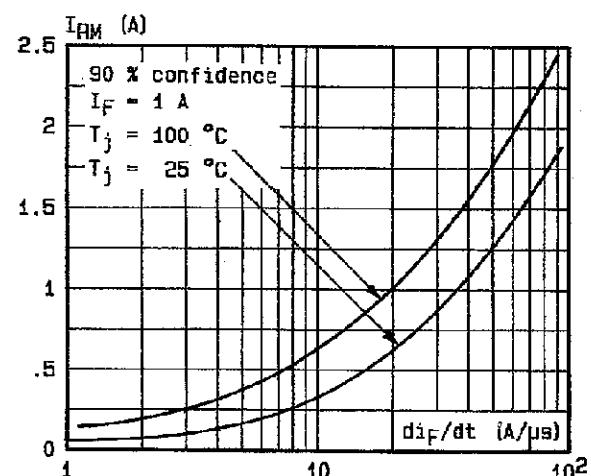


Fig.11 : Dynamic parameters versus junction temperature.

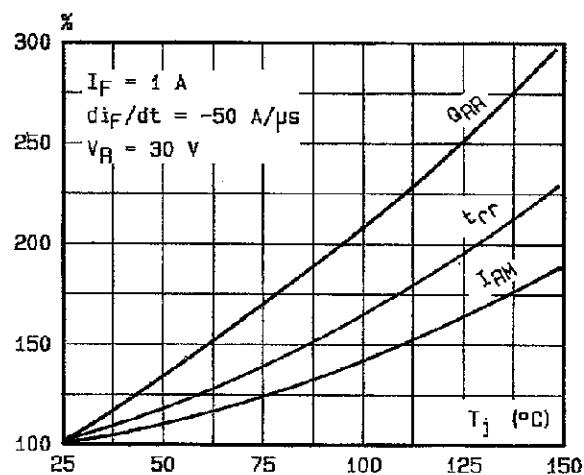


Fig.8 : Peak forward voltage versus dI_F/dt .

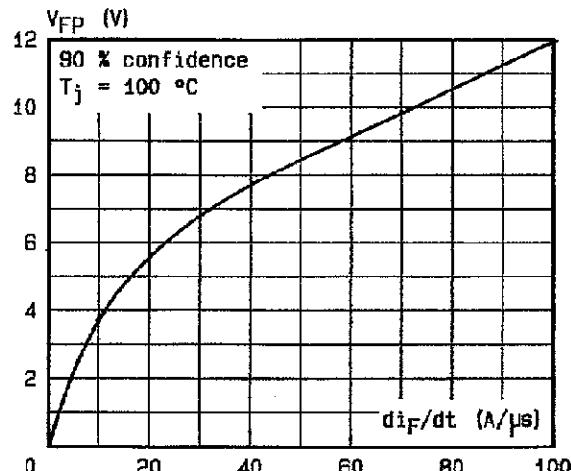


Fig.10 : Recovery charge versus dI_F/dt . (typical values)

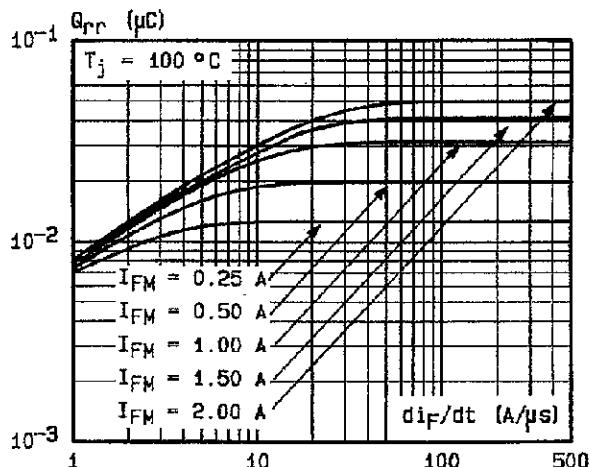
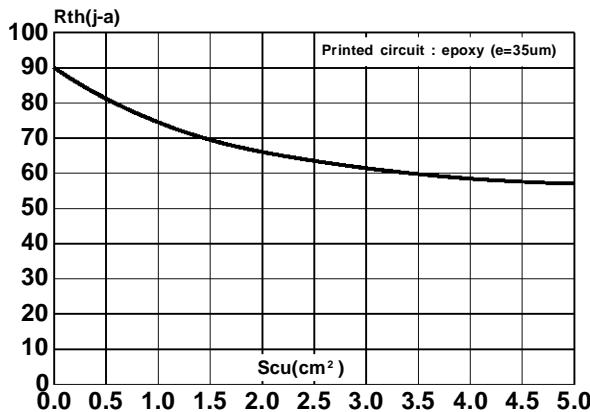
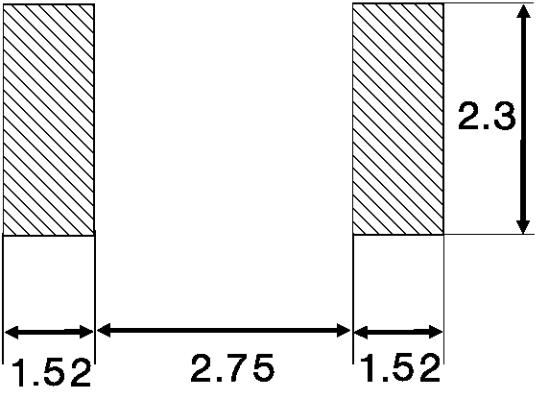
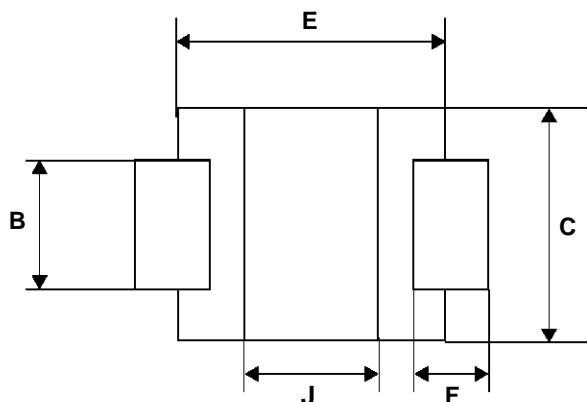
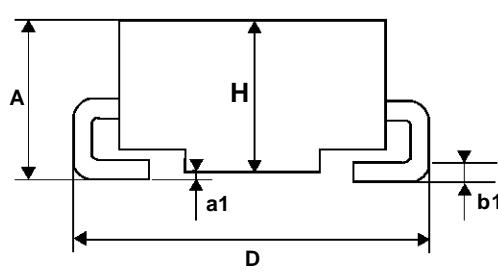


Fig.12 : Thermal resistance junction to ambient versus copper surface under each lead.



PACKAGE MECHANICAL DATA
SOD6

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.44	2.62	0.096	0.103
a1	0.10	0.20	0.004	0.008
B	1.96	2.11	0.077	0.083
b1	0.25	0.35	0.010	0.014
C	3.65	3.93	0.143	0.155
D	5.39	5.59	0.212	0.220
E	4.15	4.30	0.163	0.170
F	1.00	1.27	0.039	0.050
H	2.33	2.41	0.092	0.095
J	2.05	2.13	0.080	0.084

Laser Marking
Logo indicated cathode

SMBYT01

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